Gredmann *Group*
台灣格雷蒙股份有限公司
偉斯企業股份有限公司
9F, No. 170 Sec. 3, Min Chuan East Road, Taipei, Taiwan
Tel : 886-2-2719-3456 (20 lines) **Fax** : 886-2-2716-5500 (3 Lines)
Web Site : www.gredmann.com

Wafers

1. Silicon wafer

Parameter	UOM	2"	4"	4”
Crystal Orientation:	----	<100>	<100>	<100>
Type / Dopant:	----	P / Born	P / Born	P / Born
Crystal Method:	----	CZ	CZ	CZ
Slice Orientation:	degree	0^o±0.5^o	0^o±0.5^o	0^o±0.5^o
Diameter:	mm	50.8±0.3	100±0.3	100±0.3
Thickness:	μm	430±20	430±20	625±20
Resistivity:	Ohm-cm	<0.0015	<0.0015	<0.0015
Polish:	----	SSP	SSP	SSP
Primary Flat:	mm	16±1	32±2	32±2

2. GaAs wafer

Parameter	UOM	Customer’s Requirements
Diameter	inch	2", 4", 6"
Growth Method:	----	VGF
Conduct Type:	----	S-C-N
Dopant:	----	GaAs-Si
Orientation:	----	(100)2^o, 6^o, 15^o ± 0.5^o off toward (011)
OF location/length:	----	EJ [0-1-1]± 0.5^o /32.5±1
IF location/length:	----	EJ [0-1 1]± 0.5^o/18±1
EPD:	----	Max: 5000
Thickness:	μm	350±25
Edge Rounding:	mmR	0.25
TTV/TIR:	μm	Max: 15
Surface Finish–front:	----	Polished
Surface Finish –back:	----	Etched
Partical Count:	----	＜50 (size＞ 0.3μm,Count/wafer)
Epi-Ready:	----	Yes